

512Kx32 SRAM 3.3V MODULE

FEATURES

- Access Times of 70, 85, 100, 120ns
- Packaging
 - 66-pin, PGA Type, 1.185 inch square, Hermetic Ceramic HIP (Package 401)
 - 68 lead, Hermetic CQFP (G2T), 22.4mm (0.880 inch), 4.57mm (0.180") high (Package 510). Designed to fit JEDEC 68 lead 0.990" CQFJ footprint
- Organized as 512Kx32; User Configurable as 1024Kx16 or 2Mx8
- Commercial, Industrial and Military Temperature Ranges
- TTL Compatible Inputs and Outputs
- Low Voltage Operation:
 - 3.3V ± 10% Power Supply
- Low Power CMOS
- Built-in Decoupling Caps and Multiple Ground Pins for Low Noise Operation
- Weight
 - WS512K32V-XG2TX - 8 grams typical
 - WS512K32V-XHX - 13 grams typical

* This product is under development, is not qualified or characterized and is subject to change or cancellation without notice.

PIN CONFIGURATION FOR WS512K32NV-XHX

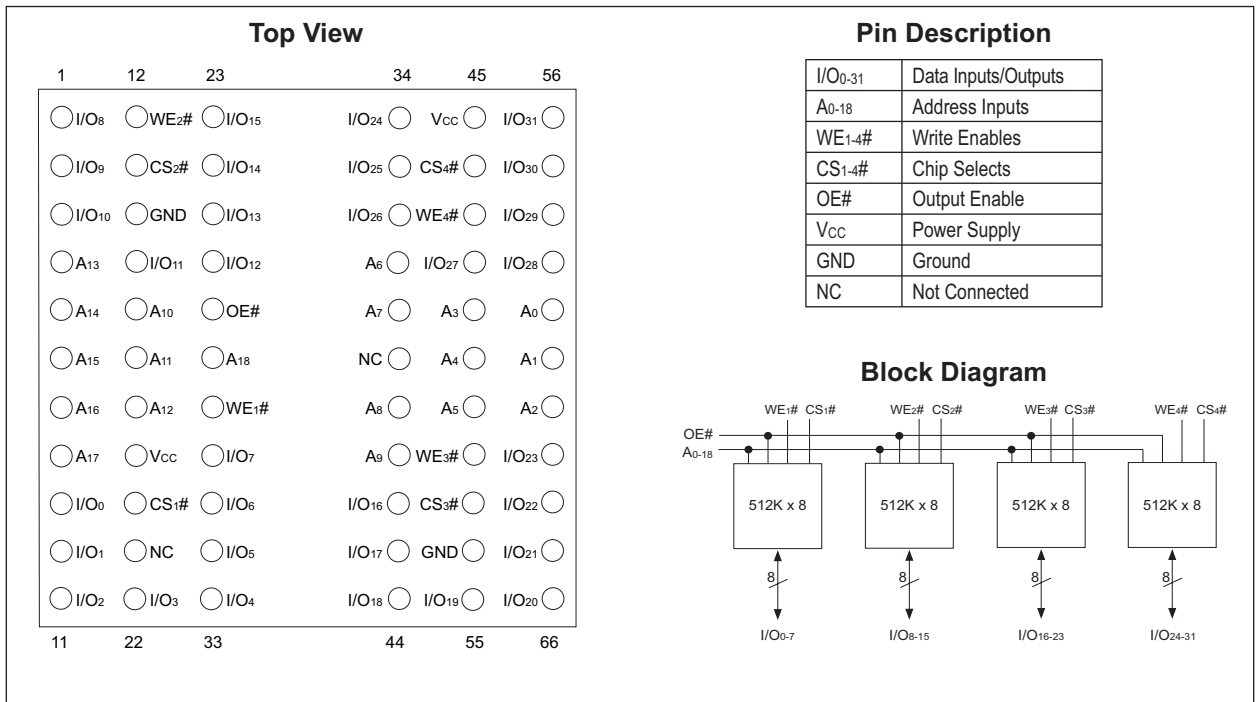
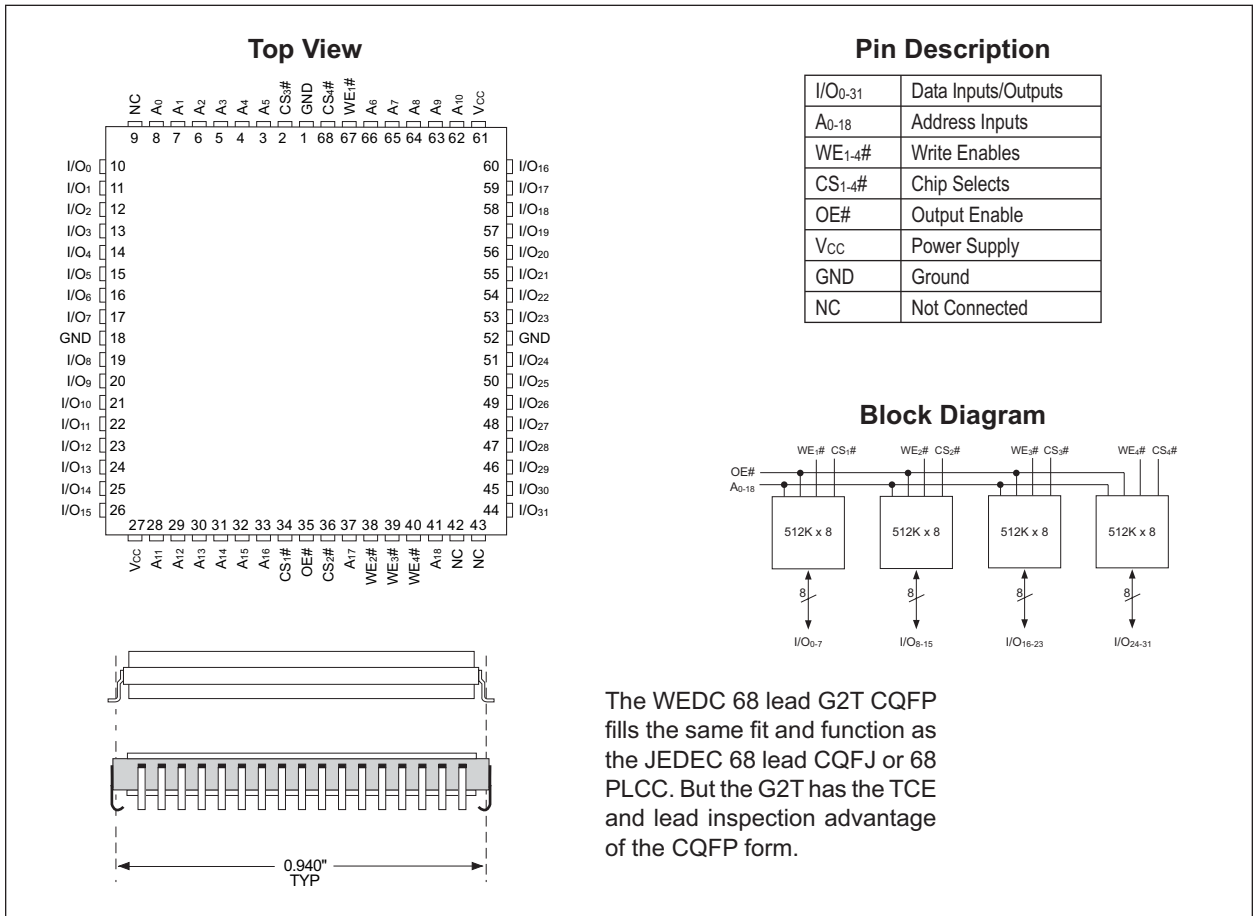




FIGURE 2 – PIN CONFIGURATION FOR WS512K32V-XG2TX





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	V _{CC} + 0.5	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	4.6	V

TRUTH TABLE

CS#	OE#	WE#	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	H	H	Out Disable	High Z	Active
L	X	L	Write	Data In	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	3.0	3.6	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V
Operating Temperature (Mil)	T _A	-0.5	+125	°C

CAPACITANCE

T_A = +25°C

Parameter	Symbol	Conditions	Max	Unit
OE# capacitance	C _{OE}	V _{IN} = 0V, f = 1.0 MHz	50	pF
WE ₁₋₄ # capacitance HIP (PGA)	C _{WE}	V _{IN} = 0V, f = 1.0 MHz	20	pF
CQFP G2U			15	
CS# capacitance	C _{CS}	V _{IN} = 0V, f = 1.0 MHz	20	pF
Data# I/O capacitance	C _{I/O}	V _{I/O} = 0V, f = 1.0 MHz	20	pF
Address input capacitance	C _{AD}	V _{IN} = 0V, f = 1.0 MHz	50	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Sym	Conditions			Units
			Min	Max	
Input Leakage Current	I _{LI}	V _{CC} = 3.6, V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	CS# = V _{IH} , OE# = V _{IH} , V _{OUT} = GND to V _{CC}		10	μA
Operating Supply Current	I _{CC x 32}	CS# = V _{IL} , OE# = V _{IH} , f = 5MHz, V _{CC} = 3.6		100	mA
Standby Current	I _{SB}	CS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 3.6		2.0	mA
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA, V _{CC} = 3.0		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -1.0mA, V _{CC} = 3.0	2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V.



AC CHARACTERISTICS

V_{CC} = 3.3V, GND = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	70		85		100		120		ns
Address Access Time	t _{AA}		70		85		100		120	ns
Output Hold from Address Change	t _{OH}	5		5		5		5		ns
Chip Select Access Time	t _{ACS}		70		85		100		120	ns
Output Enable to Output Valid	t _{OE}		35		40		50		60	ns
Chip Select to Output in Low Z	t _{CLZ} ¹	10		10		10		10		ns
Output Enable to Output in Low Z	t _{OLZ} ¹	5		5		5		5		ns
Chip Disable to Output in High Z	t _{CHZ} ¹		25		25		35		35	ns
Output Disable to Output in High Z	t _{OHZ} ¹		25		25		35		35	ns

1. This parameter is guaranteed by design but not tested.

AC CHARACTERISTICS

V_{CC} = 3.3V, GND = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	70		85		100		120		ns
Chip Select to End of Write	t _{CW}	60		75		80		100		ns
Address Valid to End of Write	t _{AW}	60		75		80		100		ns
Data Valid to End of Write	t _{DW}	30		30		40		40		ns
Write Pulse Width	t _{WP}	50		50		60		60		ns
Address Setup Time	t _{AS}	0		0		0		0		ns
Address Hold Time	t _{AH}	5		5		5		5		ns
Output Active from End of Write	t _{OW} ¹	5		5		5		5		ns
Write Enable to Output in High Z	t _{WHZ} ¹		25		25		35		35	ns
Data Hold from Write Time	t _{DH}	0		0		0		0		ns

1. This parameter is guaranteed by design but not tested.

FIGURE 3 – AC TEST CIRCUIT

The diagram shows an AC test circuit. A central component labeled 'D.U.T.' is connected to a bridge circuit. The bridge consists of four diodes. Two current sources are connected to the bridge nodes, with current flow labeled I_{OL} and I_{OH}. A bipolar supply is connected to the bridge, with a voltage V_Z ≈ 1.5V. A capacitor with C_{eff} = 50 pf is connected to the D.U.T. input.

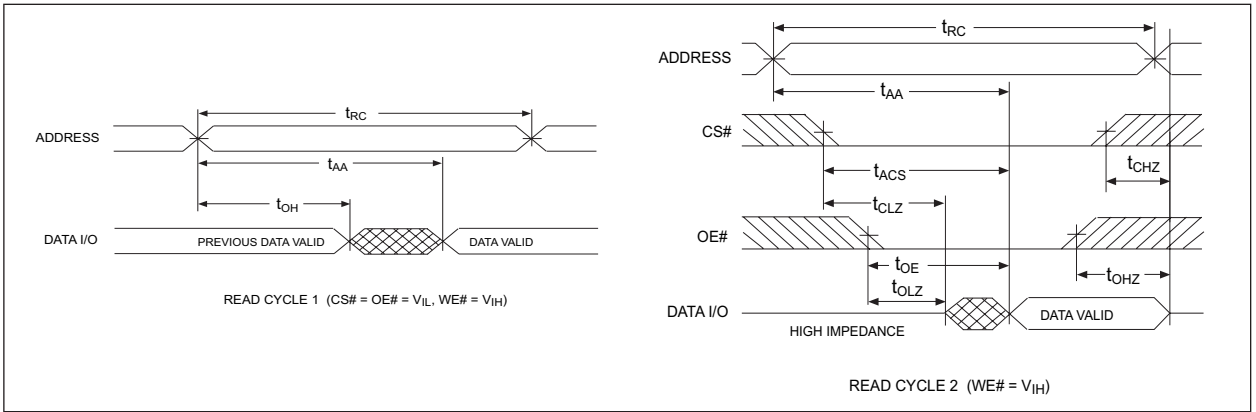
AC Test Conditions

Parameter	Typ	Unit
Input Pulse Levels	V _{IL} = 0, V _{IH} = 2.5	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

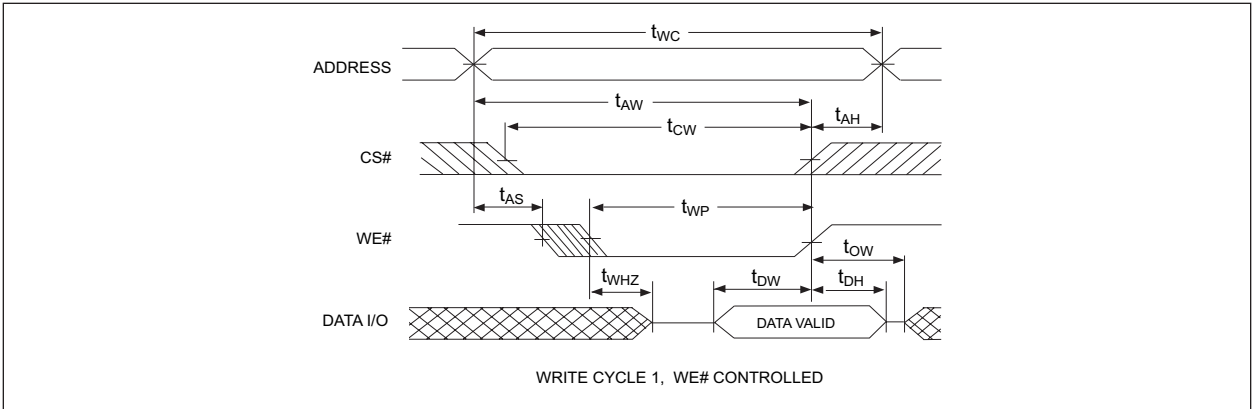
NOTES:
V_Z is programmable from -2V to +7V.
I_{OL} & I_{OH} programmable from 0 to 16mA.
Tester Impedance Z₀ = 75 Ω.
V_Z is typically the midpoint of V_{OH} and V_{OL}.
I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
ATE tester includes jig capacitance.



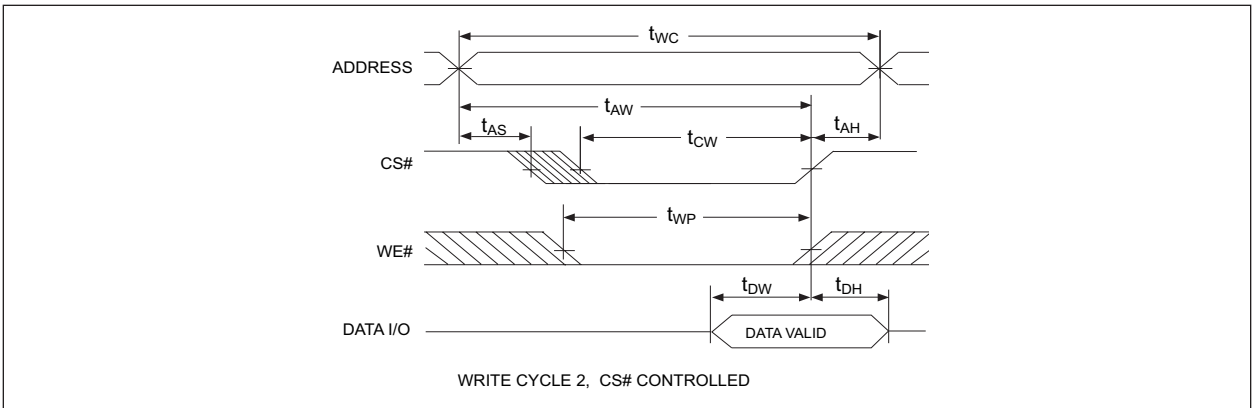
TIMING WAVEFORM – READ CYCLE



WRITE CYCLE – WE# CONTROLLED

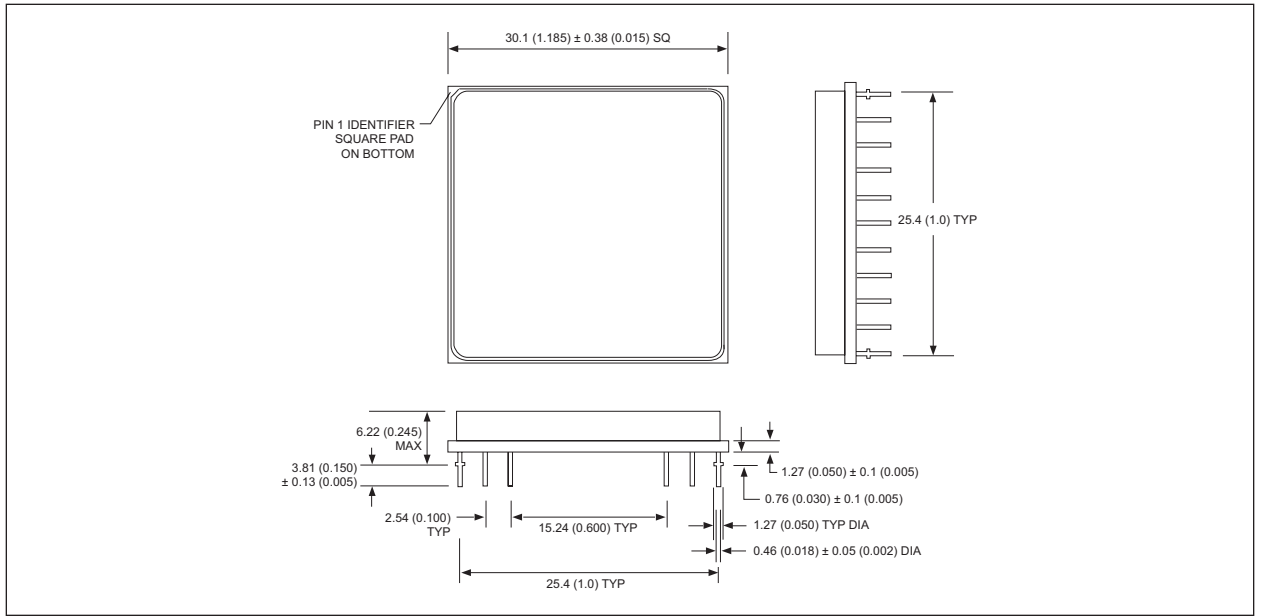


WRITE CYCLE – CS# CONTROLLED





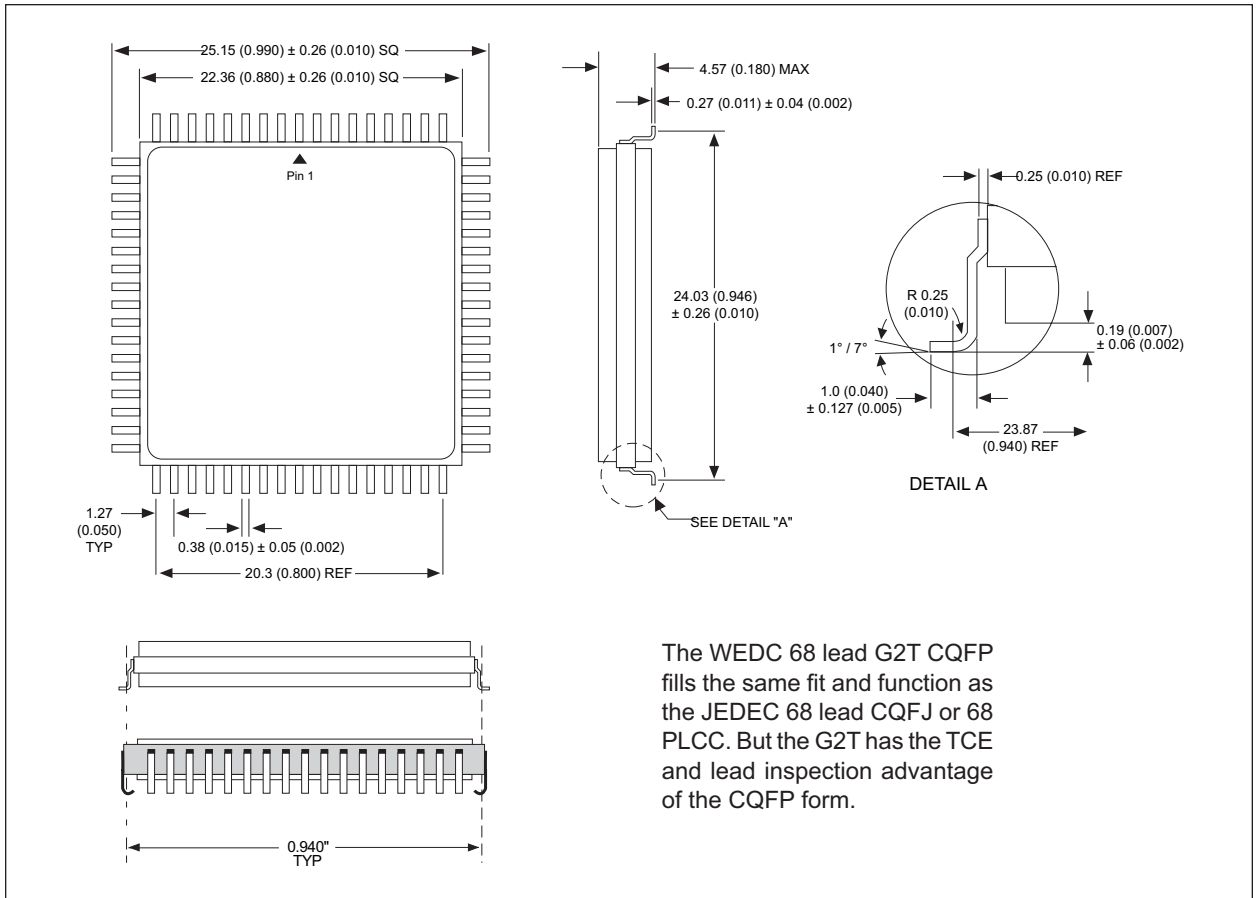
PACKAGE 401: 66 PIN, PGA TYPE, CERAMIC HEX-IN-LINE PACKAGE, HIP (H)



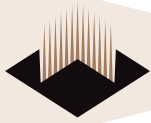
ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES



PACKAGE 509: 68 LEAD, CERAMIC QUAD FLAT PACK, CQFP (G2T)



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ORDERING INFORMATION

W S 512K 32 X V - XXX X X X

LEAD FINISH:

Blank = Gold plated leads
A = Solder dip leads

DEVICE GRADE:

M = Military -55°C to +125°C
I = Industrial -40°C to +85°C
C = Commercial 0°C to +70°C

PACKAGE TYPE:

H = Ceramic Hex In Line Package, HIP (Package 401)
G2T = 22.4mm Ceramic Quad Flat Pack, CQFP (Package 509)

ACCESS TIME (ns)

Low Voltage Supply 3.3V ± 10%

IMPROVEMENT MARK:

N = No Connect at pin 21 and 39 in HIP for Upgrades

ORGANIZATION, 512Kx32

User configurable as 1Mx16 or 2Mx8

SRAM

WHITE ELECTRONIC DESIGNS CORP.